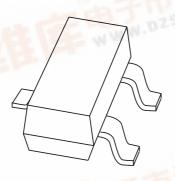
DISCRETE SEMICONDUCTORS

DATA SHEET



MMBT3906 PNP switching transistor

Product specification
Supersedes data of 2000 Apr 11







PNP switching transistor

MMBT3906

FEATURES

- Collector current capability I_C = −200 mA
- Collector-emitter voltage $V_{CEO} = -40 \text{ V}$.

APPLICATIONS

• General switching and amplification.

DESCRIPTION

PNP switching transistor in a SOT23 plastic package. NPN complement: MMBT3904.

MARKING

TYPE NUMBER	MARKING CODE(1)
MMBT3906	7B*

Note

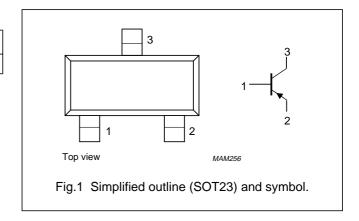
- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-40	٧
I _C	collector current (DC)	-200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V _{CEO}	collector-emitter voltage	open base	_	-40	V
V _{EBO}	emitter-base voltage	open collector	_	-6	V
I _C	collector current (DC)		_	-200	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

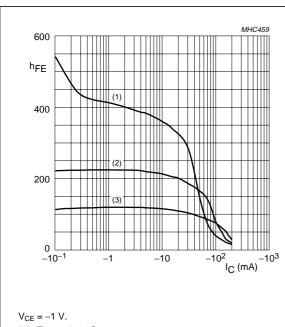
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	_	-50	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = -6 V	_	-50	nA
h _{FE}	DC current gain	V _{CE} = −1 V; see Fig.2			
		$I_{\rm C} = -0.1 \text{mA}$	60	_	
		$I_C = -1 \text{ mA}$	80	_	
		$I_{\rm C} = -10 \; {\rm mA}$	100	300	
		$I_{\rm C} = -50 \; {\rm mA}$	60	_	
		$I_{\rm C} = -100 \text{ mA}$	30	_	
V _{CEsat}	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	_	-250	mV
vo	voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	_	-400	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	_	-850	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	_	-950	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -5$ V; $f = 1$ MHz	_	4.5	pF
C _e	emitter capacitance	$I_C = I_c = 0$; $V_{EB} = -500 \text{ mV}$; $f = 1 \text{ MHz}$	_	10	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V};$ f = 100 MHz	250	_	MHz
F	noise figure	$I_C = -100 \mu A$; $V_{CE} = -5 V$; $R_S = 1 kΩ$; $f = 10 Hz$ to 15.7 kHz	_	4	dB
Switching t	imes (between 10% and 90% lev	els); see Fig.7	•		
t _d	delay time	I _{Con} = -10 mA; I _{Bon} = -1 mA;	_	35	ns
t _r	rise time	I _{Boff} = 1 mA	_	35	ns
t _s	storage time		_	225	ns
t _f	fall time		_	75	ns

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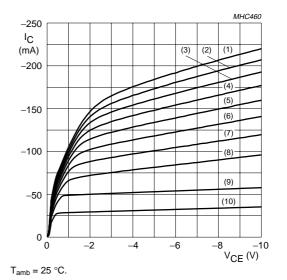


(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain; typical values.



(1) $I_B = -1.5 \text{ mA}.$

(5) $I_B = -0.9 \text{ mA}.$

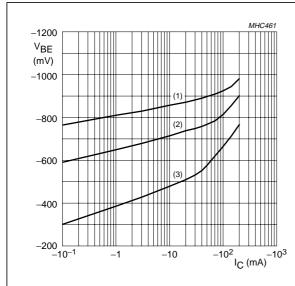
(9) $I_B = -0.3 \text{ mA}.$ (10) $I_B = -0.15 \text{ mA}$.

(2) $I_B = -1.35 \text{ mA}.$ (3) $I_B = -1.2 \text{ mA}.$

(6) $I_B = -0.75 \text{ mA}.$ (7) $I_B = -0.6 \text{ mA}.$

(4) $I_B = -1.05 \text{ mA}.$ (8) $I_B = -0.45 \text{ mA}.$

Collector current as a function of collector-emitter voltage.



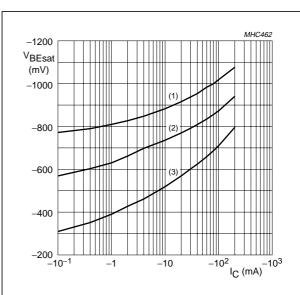
 $V_{CE} = -1 V$.

(1) $T_{amb} = -55 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = 150 \, ^{\circ}C$.

Base-emitter voltage as a function of collector current.



 $I_{\rm C}/I_{\rm B}=10$.

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(1) $T_{amb} = -55 \,^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = 150 \, ^{\circ}C$.

Base-emitter saturation voltage as a function of collector current.

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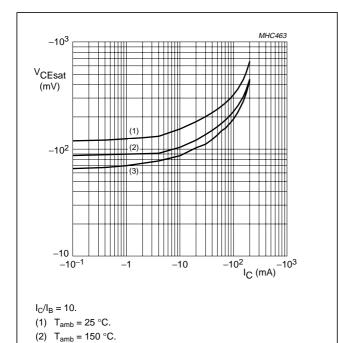
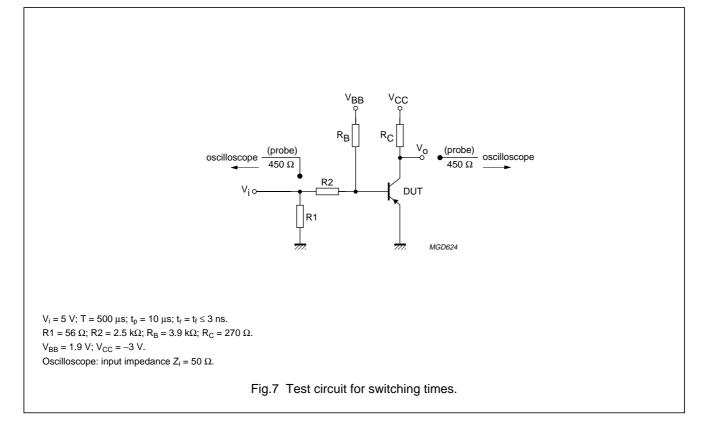


Fig.6 Collector-emitter saturation voltage as a function of collector current.

(3) $T_{amb} = -55 \, ^{\circ}C$.



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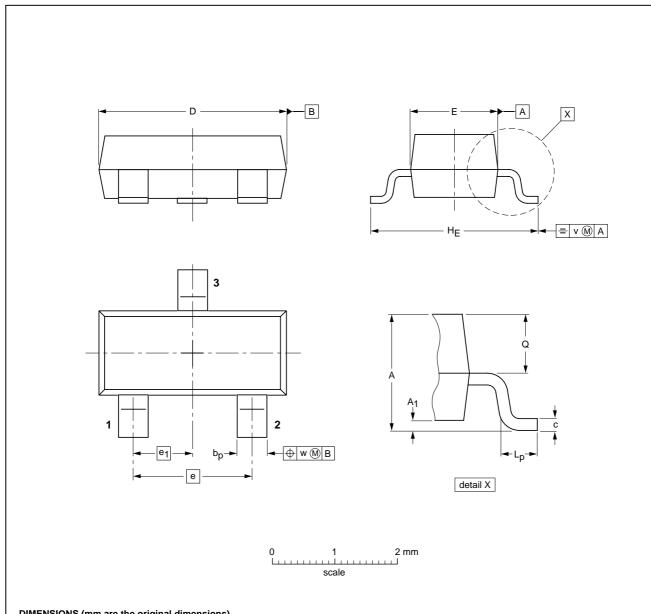
PNP switching transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-97-02-28 99-09-13

Philips Semiconductors Product specification

PNP switching transistor

MMBT3906

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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